

20V P-Channel Enhancement Mode MOSFET

General Features

- ≻ Proprietary Advanced Planar Technology
- Rugged Polysilicon Gate Cell Structure ≻
- ≻ Fast Switching Speed
- ≻ **RoHS** Compliant
- Halogen-free Available >

Applications

- High Efficiency SMPS ≻
- Adaptor/Charger ≻
- Active PFC ≻

BV _{DSS}	R _{DS(ON)} (Typ.)	ID			
-20V	5.2Ω	-280mA			



Ordering Information

Part Number	Package	Marking	Remark		
FTZ50P01G5	SOT-23	P01	Halogen Free		

Absolute Maximum Ratings

Absolute Maximum Ratings		$T_A=25^{\circ}C$ unless otherwise	e specified	
Symbol	Parameter	FTZ50P01G5	Unit	
V _{DSS}	Drain-to-Source Voltage ^[1]	-20	V	
I _D	Continuous Drain Current	-0.28		
I _{DM}	Pulsed Drain Current ^[2]	-1.12	A	
P _D	Power Dissipation	0.5	W	
V _{GS}	Gate-to-Source Voltage	±20	V	
T_L	Soldering Temperature Distance of 1.6mm from case for 10 seconds	300	°C	
T_J and T_{STG}	Operating and Storage Temperature Range	-55 to 150		

Caution: Stresses greater than those listed in the "Absolute Maximum Ratings" may cause permanent damage to thedevice.

Thermal Characteristics

Symbol	Parameter	FTZ50P01G5	Unit
$R_{ heta JA}$	Thermal Resistance, Junction-to-Ambient	250	K/W

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Electrical Characteristics

OFF Characteristics

OFF Characteristics					$T_A = 25 ^{\circ}C$ unless otherwise specified		
Symbol	Parameter	Min.	Тур.	Max.	Unit	Test Conditions	
BV _{DSS}	Drain-to-Source Breakdown Voltage	-20			V	$V_{GS}=0V, I_{D}=-250 \mu A$	
I _{DSS}	Drain-to-Source Leakage Current		-0.23		nA	V_{DS} =-10V, V_{GS} =0V	
I _{GSS}	Gate-to-Source Leakage Current		2		nA	V_{GS} =+20V, V_{DS} =0V	
			-3			V_{GS} =-20V, V_{DS} =0V	

ON Characteristics

 $T_A = 25 \degree C$ unless otherwise specified

Symbol	Parameter	Min.	Тур.	Max.	Unit	Test Conditions
R _{DS(ON)}	Static Drain-to-Source On-Resistance		5.2		Ω	V_{GS} =-10V, I_D =-50mA ^[3]
V _{GS(OFF)}	Gate-to-Source Cut-off Voltage		-4.38		V	$V_{GD}=0V, I_D=-1\mu A$
			-5.24		V	V _{GD} =0V, I _D =-250µA

Source-Drain Diode Characteristics T _A =25 °C unless otherwise spec					5°C unless otherwise specified	
Symbol	Parameter	Min	Тур.	Max.	Units	Test Conditions
V _{SD}	Diode Forward Voltage		1.13		V	I_{SD} =-50m $A^{[3]}$, V_{GS} =0V

NOTE:

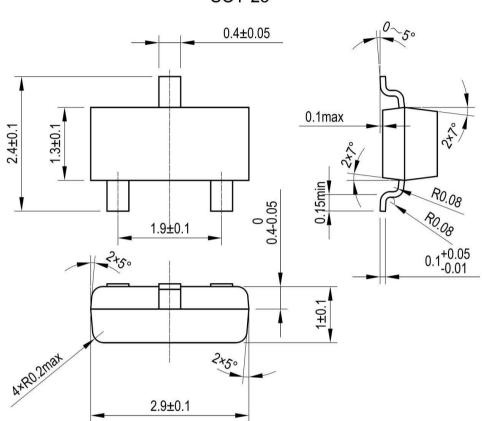
[1] T_J=+25°C to +150°C

[2] Repetitive rating, pulse width limited by maximum junction temperature. [3] Pulse width \leq 380µs; duty cycle \leq 2%.

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Package Dimensions



SOT-23

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